

## Product Summary

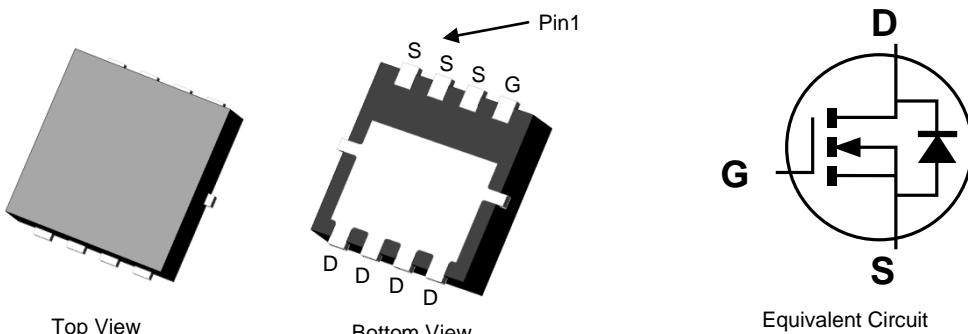
BV <sub>DSS</sub>	R <sub>DSON</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
30V	7mΩ @ V <sub>GS</sub> = 10V	60A
	11mΩ @ V <sub>GS</sub> = 4.5V	

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DSON</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Power Management Functions
- Analog Switch



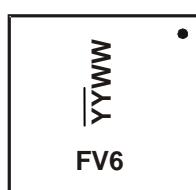
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3006LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMT3006LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



FV6 = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Two Digits of Year (ex: 17 = 2017)  
WW = Week Code (01 to 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 7)	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	$I_D$	60 45	A
Maximum Body Diode Forward Current (Note 7)			$I_S$	2	A
Pulsed Drain Current (380 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	90	A
Pulsed Drain Body Diode Forward Current (380 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{SM}$	90	A
Avalanche Current ( $L = 0.1\text{mH}$ ) (Note 8)			$I_{AS}$	24	A
Avalanche Energy ( $L = 0.1\text{mH}$ ) (Note 8)			$E_{AS}$	29	$\text{mJ}$

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			$P_D$	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	130	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)			$P_D$	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	63	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 7)			$R_{\theta JC}$	2.9	
Operating and Storage Temperature Range			$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = +20\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = -16\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	5.6	7	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 9.0\text{A}$
			8.0	11		$V_{GS} = 4.5\text{V}, I_D = 8.5\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.70	1.2	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	$C_{ISS}$	—	1,155	—	$\text{pF}$	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	456	—		
Reverse Transfer Capacitance	$C_{RSS}$	—	72	—		
Gate Resistance	$R_g$	—	1.6	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	—	16.7	—	$\text{nC}$	$V_{DD} = 15\text{V}, I_D = 9\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_g$	—	8.4	—		
Gate-Source Charge	$Q_{GS}$	—	2.2	—		
Gate-Drain Charge	$Q_{GD}$	—	3.5	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	$\text{ns}$	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_g = 3\Omega, I_D = 9\text{A}$
Turn-On Rise Time	$t_R$	—	5.5	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	13.5	—		
Turn-Off Fall Time	$t_F$	—	4.6	—		
Reverse Recovery Time	$t_{RR}$	—	19.3	—	$\text{ns}$	$I_F = 1.5\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{RR}$	—	8.6	—		

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- Thermal resistance from junction to soldering point (on the exposed drain pad).
- $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .
- Short duration pulse test used to minimize self-heating effect.
- Guaranteed by design. Not subject to product testing.

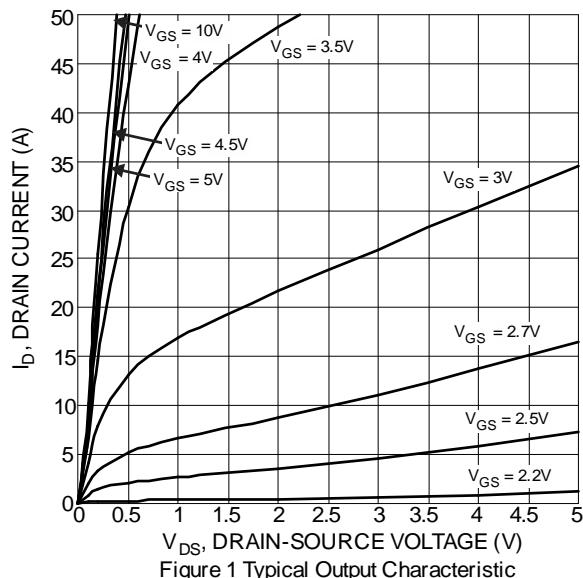


Figure 1 Typical Output Characteristic

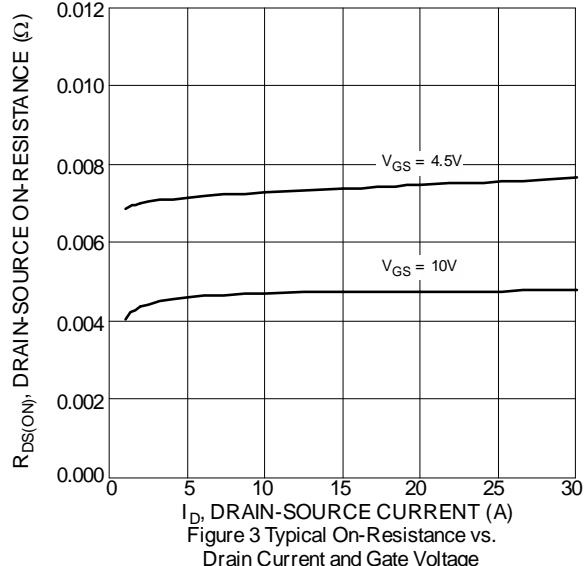


Figure 3 Typical On-Resistance vs.  
Drain Current and Gate Voltage

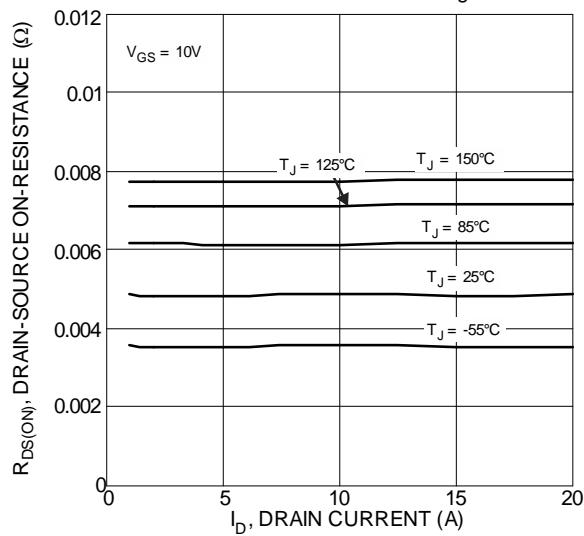


Figure 5 Typical On-Resistance vs.  
Drain Current and Temperature

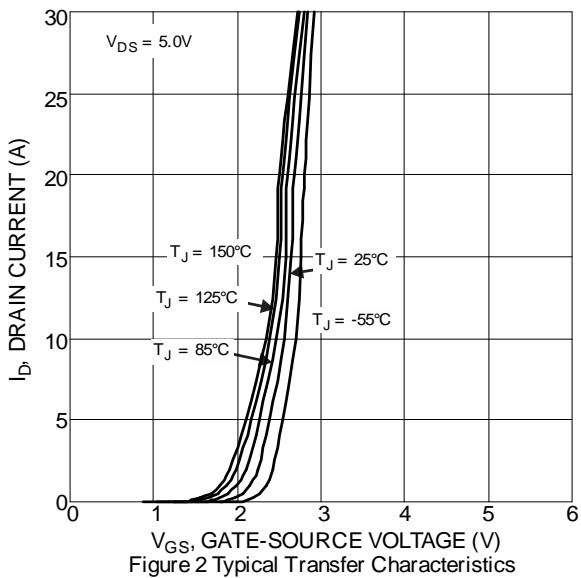


Figure 2 Typical Transfer Characteristics

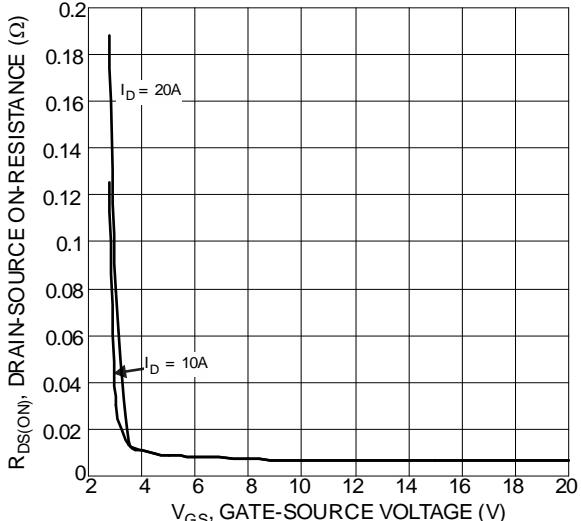


Figure 4 Typical Drain-Source On-Resistance  
vs. Gate-Source Voltage

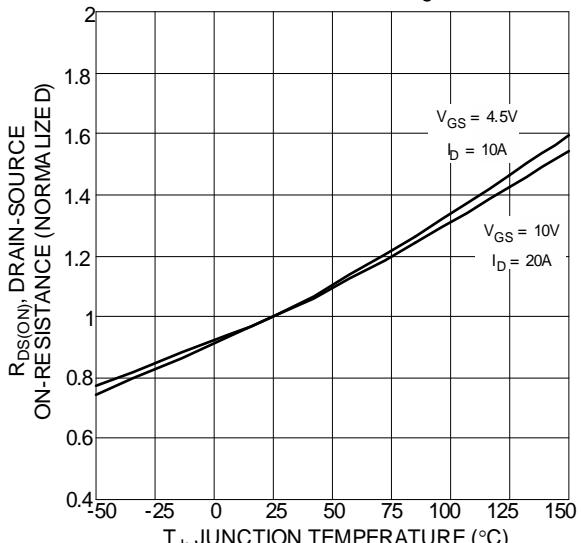
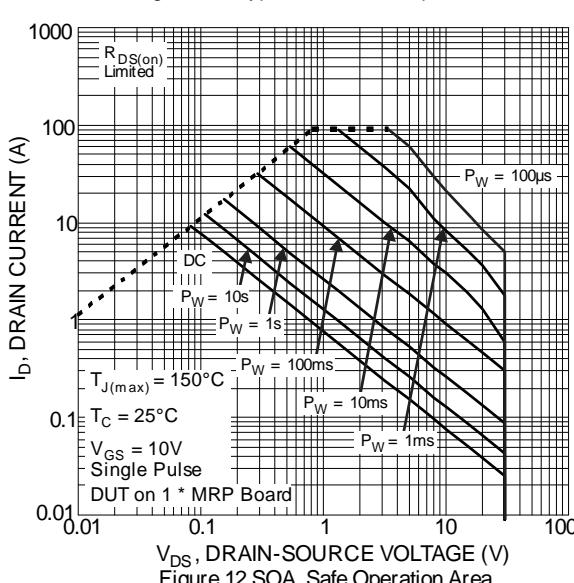
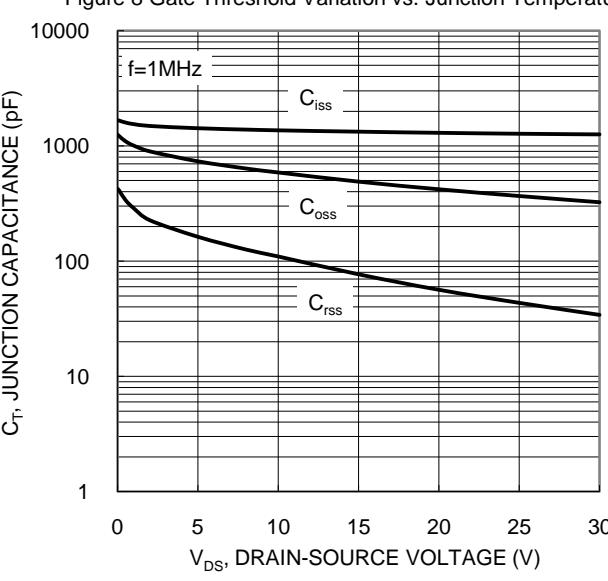
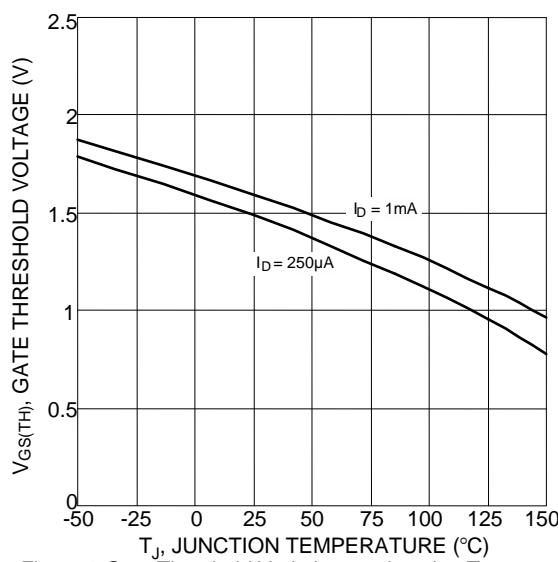
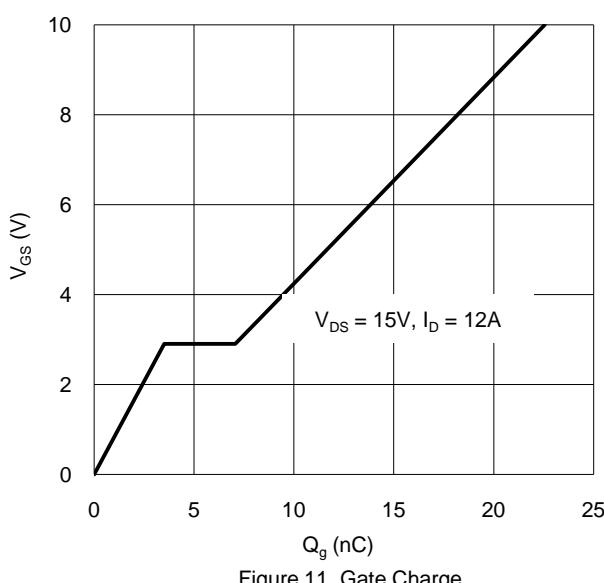
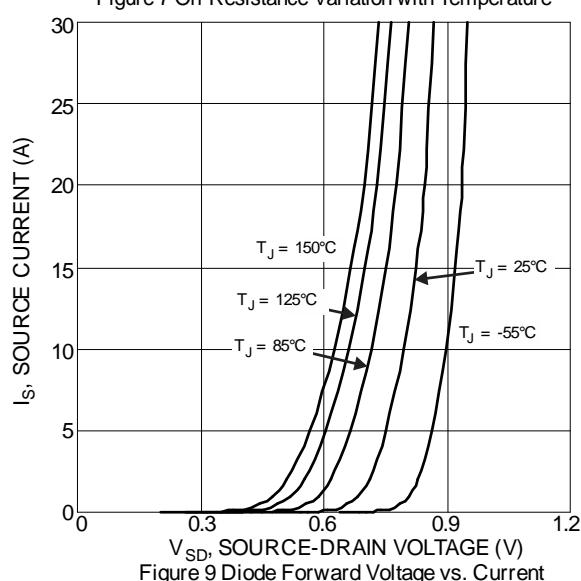
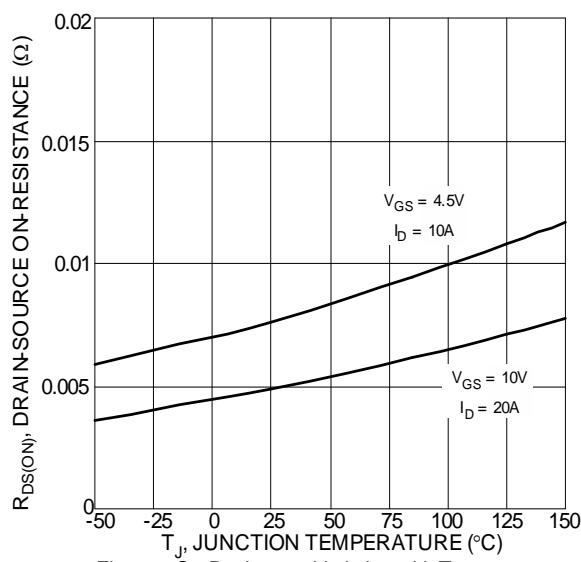


Figure 6 On-Resistance Variation with Temperature



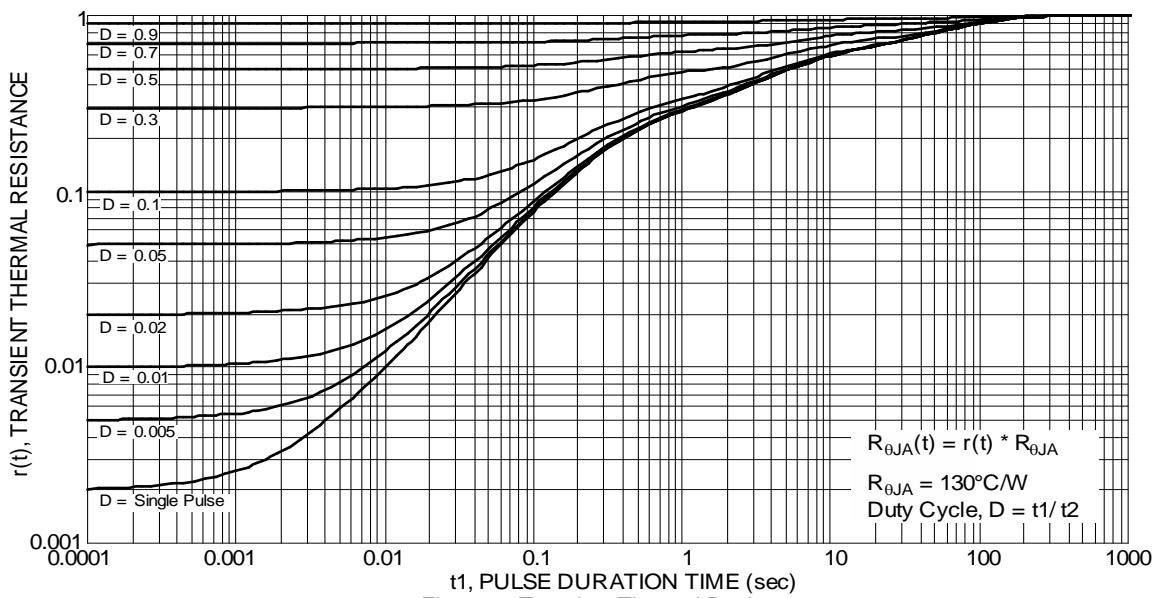
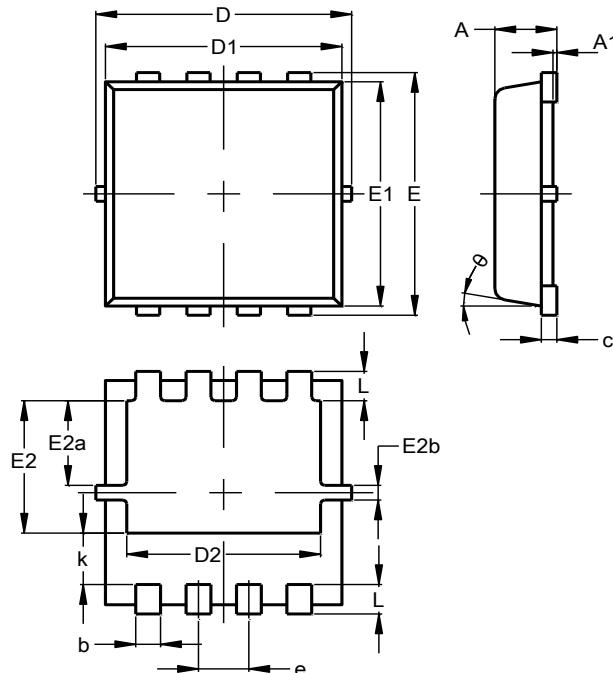


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (Type UX)



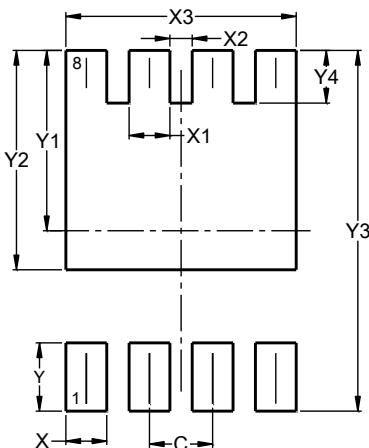
PowerDI3333-8 (Type UX)			
Dim	Min	Max	Typ
<b>A</b>	0.75	0.85	0.80
<b>A1</b>	0.00	0.05	--
<b>b</b>	0.25	0.40	0.32
<b>c</b>	0.10	0.25	0.15
<b>D</b>	3.20	3.40	3.30
<b>D1</b>	2.95	3.15	3.05
<b>D2</b>	2.30	2.70	2.50
<b>E</b>	3.20	3.40	3.30
<b>E1</b>	2.95	3.15	3.05
<b>E2</b>	1.60	2.00	1.80
<b>E2a</b>	0.95	1.35	1.15
<b>E2b</b>	0.10	0.30	0.20
<b>e</b>	0.65 BSC		
<b>k</b>	0.50	0.90	0.70
<b>L</b>	0.30	0.50	0.40
<b>θ</b>	0°	12°	10°

All Dimensions in mm

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
<b>C</b>	0.650
<b>X</b>	0.420
<b>X1</b>	0.420
<b>X2</b>	0.230
<b>X3</b>	2.370
<b>Y</b>	0.700
<b>Y1</b>	1.850
<b>Y2</b>	2.250
<b>Y3</b>	3.700
<b>Y4</b>	0.540

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